

In the Specification:

Please **replace** the paragraph at **page 13, lines 10 to 25** , with a replacement paragraph amended as follows:

In addition, as shown in examples ~~[[4-8,]]~~ 4-13, highly accurate surface processing with the maximum depth of the surface scratch less than 0.01 μm and the average thickness of the damaged layer less than 1 μm is also possible using Li or Ca in place of or in combination with Na as the processing solution. In particular, as shown in examples 6, 8, ~~[[10-11]]~~ and 12-14, the processing speed is increased and the processing time can be decreased when the processing solution containing at least Li is used. In addition, as is obvious from ~~example 9~~ example 15 in comparison with example 2, the processing time can be decreased from 5 hours to 1 hour when the surface plate having the grooves on the processing surface is used in place of the surface plate having a flat processing surface. In addition, as shown in ~~examples 10-12,~~ examples 16-18, highly accurate surface processing with the maximum depth of the surface scratch less than 0.01 μm and the average thickness of the damaged layer less than 1 μm is enabled by setting the processing time to 20-3 hours as appropriate for the processing temperature of 300-1000 $^{\circ}\text{C}$. Furthermore, as shown in ~~examples 13-16,~~ examples 19-22, the crystal to be processed is not limited to the GaN crystal, and highly accurate surface processing of each kind of nitride semiconductor crystal such as an AlN crystal, an AlGaIn crystal, an InN crystal, or an InGaIn crystal is also possible.